## UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO.

: 6,930,862 B2

: August 16, 2005

DATED

INVENTOR(S) : Gill et al.

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

## Title page,

Item [56], References Cited, U.S. PATENT DOCUMENTS, add the following patent numbers:

-- 6,117,690

5,965,283

5,699,215

5,422,621

4,371,905

4,935,832 --.

FOREIGN PATENT DOCUMENTS, add the following publication number:

-- WO 01/41214 A1

06/2001

WIPO ..... 23/58 --.

OTHER PUBLICATIONS, add the following citations:

-- Solin, S.A. et al; Enhanced Room-Temperature Geometric Magnetoresistance in Inhomogeneous Narrow-Gap Semiconductors, SCIENCE Vol. 289, 09/01/2000.

Solin, S.A. et al; Enhanced Room-Temperature Geometric Magnetoresistance in Inhomogeneous Narrow-Gap Semiconductors, The Magnetic Recording Conference, August 20-22, 2001.

Isai, Masaaki et al; Preparation and Crystal Properties of Thin InSb Films for Highly Sensitive Magnetoresistance Elements, Journal of Materials Research, 1986. ---

Chi, C. et al; Gradiometer Hall Probe, IBM Technical Disclosure Bulletin, Vol. 37 04/1994.

Gambino, R. et al; Improved Magnetoresistive Sensor, IBM Technical Disclosure Bulletin, Vol. 38, No. 08, August 1995.

Gambino, R. et al; Magnetic Films for Hall Effect Devices Useful for Magnetic Recording Heads, IBM Technical Disclosure Bulletin, Vol. 18, No. 12, May 1976. --

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Page 2 of 2

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Column 8,

Line 9, after "of the EMR" delete "read".

Signed and Sealed this

Thirteenth Day of December, 2005

JON W. DUDAS Director of the United States Patent and Trademark Office